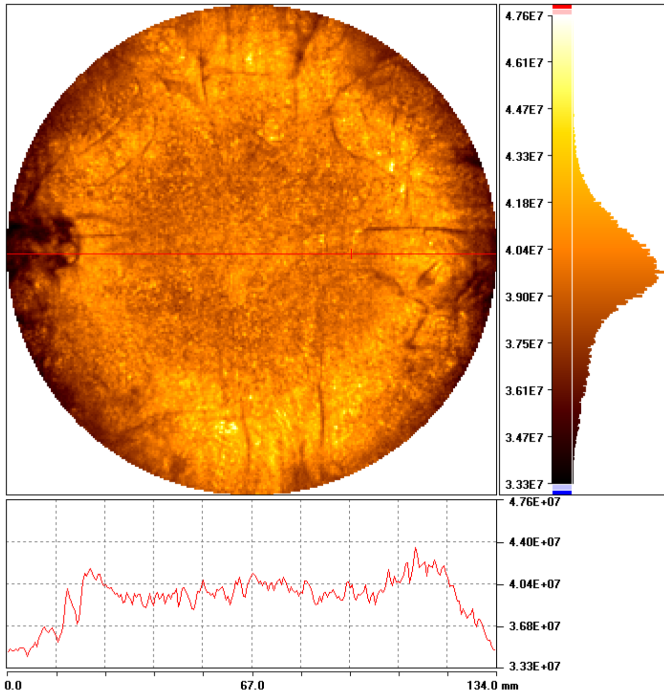
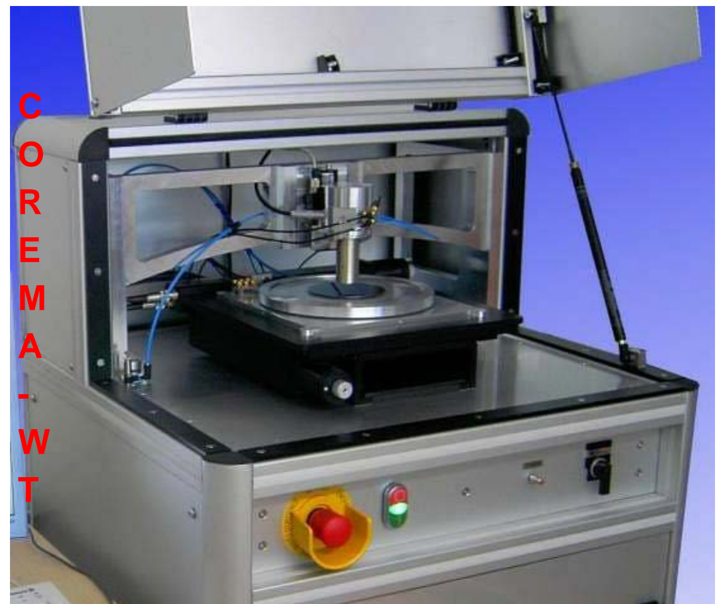
C O R E M A

Contactless Resistivity Mapping and Mobility Measurements for Semi-Insulating Substrates



- GaAs, InP, SiC, GaN, Cd(Zn)Te
- Rapid Full Wafer High Resolution Resistivity Topography
- Resistivity Range: $1x10^5$ - $1x10^{12}$ Ohm-cm
- Fast, 1% Repeatability

- Non-Destructive Measurements
- No Sample Preparation
- Wafer Sizes up to 150/200mm
- For Wafer Production and Process Development



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Replaces Slow, Destructive Hall Measurement

- No Sample Preparation
- No Loss of Wafer Material
- Rapid Mobility Measurement (<1 min)
- High Lateral Resolution (1mm)
- Non-Contact
- Excellent Repeatability

COREMA Series System Options

Configuration	Measurement Capability
COREMA - *WT*	* Measure substrate resistivity. * Automated full wafer resistivity topography mapping.
COREMA - *RM*	* Measure substrate carrier concentration, mobility, and resistivity. * Manual multi-point measurement.
COREMA - *ER*	* Measure epitaxial buffer layer resistance * Example: GaN layers on SiC or sapphire substrates.
COREMA - *VT*	* Measure substrate resisitivity at variable temperature up to 673K/400C. * Evaluate activation energy.